

ABSTRACT OF THE DISCLOSURE

A semiconductor device according to the present invention includes:
a semiconductor substrate including an active region and an isolation
region; a gate electrode formed on the active region with an oxide film
interposed therebetween; and a set of impurity regions formed on both
5 sides of the gate electrode. A surface of the active region is entirely
rounded so as to be inclined downward toward the isolation region. This
rounded shape can be formed by forming an isolation oxide film such that a
bird's beak portion is connected on the active region.